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1N2804 thru 1N2846B and 1N4557B thru 1N4564B

SILICON
50 WATT
ZENER DIODES

FEATURES

- ZENER VOLTAGE 3.9V to 200V
- AVAILABLE IN TOLERANCES OF ±5%, ±10% and ±20%
- DESIGNED FOR MILITARY ENVIRONMENTS (See Below)

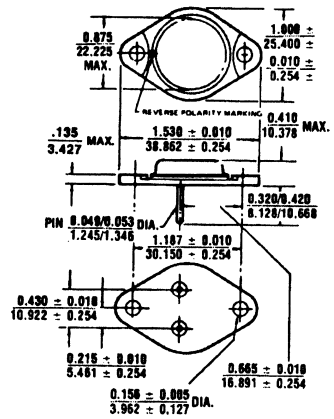
MAXIMUM RATINGS

Junction and Storage Temperatures: −65°C to +175°C
DC Power Dissipation: 50 watts
Power Derating: 0.5W/°C above 75°C
Forward Voltage @ 10 A: 1.5 Volts

*ELECTRICAL CHARACTERISTICS @ 25°C

JEDEC TYPE NO. (Note 1)	NOMINAL ZENER VOLTAGE V_z @ I_{zt} Volts (Note 2)	ZENER TEST CURRENT (I_{zt}) mA	MAX. ZENER IMPEDANCE (Note 3) Z_{zt} @ I_{zt} OHMS	Z_{zk} @ 5 mA (I_{zk}) OHMS	MAX. DC ZENER CURRENT (I_{zm}) @ 75°C Case Temp. (Note 4) mA	TYPICAL ZENER VOLTAGE Temp. Coeff. α_{vz} %/°C	MAXIMUM LEAKAGE CURRENT ** I_R @ V_R µA	V
†1N4557B	3.9	3200	0.16	400	11,900	−0.046	150	0.5
†1N4558B	4.3	2900	0.16	500	10,650	−0.033	150	0.5
†1N4559B	4.7	2650	0.12	600	9,700	−0.015	100	1
†1N4560B	5.1	2450	0.12	650	8,900	±0.010	20	1
†1N4561B	5.6	2250	0.12	900	8,100	+0.03	20	1
†1N4562B	6.2	2000	0.14	1000	7,300	+0.049	20	2
1N4563B	6.8	1850	0.16	200	6,650	+0.053	10	2
1N4564B	7.5	1650	0.24	100	6,050	+0.057	10	3
†1N2804B	6.8	1850	0.2	70	7,400	.040	150	4.5
†1N2805B	7.5	1700	0.3	70	6,600	.045	100	5
†1N2806B	8.2	1500	0.4	70	5,800	.048	50	5.4
†1N2807B	9.1	1370	0.5	70	5,300	.050	25	6.1
†1N2808B	10	1200	0.6	80	4,800	.055	25	6.7
†1N2809B	11	1100	0.8	80	4,300	.060	10	8.4
†1N2810B	12	1000	1.0	80	4,000	.065	10	9.1
†1N2811B	13	960	1.1	80	3,700	.065	10	9.9
1N2812B	14	890	1.2	80	3,400	.070	10	10.6
†1N2813B	15	830	1.4	80	3,100	.070	10	11.4
†1N2814B	16	780	1.6	80	2,950	.070	10	12.2
1N2815B	17	740	1.8	80	2,750	.075	10	13.0
†1N2816B	18	700	2.0	80	2,550	.075	10	13.7
1N2817B	19	660	2.2	80	2,450	.075	10	14.4
†1N2818B	20	630	2.4	80	2,350	.075	10	15.2
†1N2819B	22	570	2.5	80	2,100	.080	10	16.7
†1N2820B	24	520	2.6	80	1,950	.080	10	18.2
1N2821B	25	500	2.7	90	1,850	.080	10	19
†1N2822B	27	460	2.8	90	1,650	.085	10	20.6
†1N2823B	30	420	3.0	90	1,550	.085	10	22.8
†1N2824B	33	380	3.2	90	1,450	.085	10	25.1
†1N2825B	36	350	3.5	90	1,300	.085	10	27.4
†1N2826B	39	320	4.0	90	1,175	.090	10	29.7
†1N2827B	43	290	4.5	90	1,075	.090	10	32.7
1N2828B	45	280	4.5	100	1,030	.090	10	34.2
†1N2829B	47	270	5.0	100	980	.090	10	35.8
1N2830B	50	250	5.0	100	935	.090	10	38
†1N2831B	51	245	5.2	100	925	.090	10	38.8
†1N2832B	56	220	6	110	825	.090	10	42.6
†1N2833B	62	200	7	120	735	.090	10	47.1
†1N2834B	68	180	8	140	670	.090	10	51.7
†1N2835B	75	170	9	150	600	.090	10	56
†1N2836B	82	150	11	160	550	.090	10	62.2
†1N2837B	91	140	15	180	470	.090	10	69.2
†1N2838B	100	120	20	200	450	.090	10	76
1N2839B	105	120	25	210	430	.095	10	79.8
†1N2840B	110	110	30	220	410	.095	10	83.6
†1N2841B	120	100	40	240	375	.095	10	91.2
†1N2842B	130	95	50	275	345	.095	10	98.8
†1N2843B	150	85	75	400	300	.095	10	114.0
†1N2844B	160	80	80	450	285	.095	10	121.6
†1N2845B	180	68	90	525	250	.095	10	136.8
†1N2846B	200	65	100	600	220	.100	10	152.0

*JEDEC Registered Data. **Not JEDEC Data.
†Have JAN, JANTX and JANTXV Qualifications to MIL-S-19500/114.



All dimensions in INCH / m.m. FIGURE 1

MECHANICAL CHARACTERISTICS

CASE: Industry Standard TO-3, (modified), hermetically sealed, 0.052 inch diameter pins.

FINISH: All external surfaces are corrosion resistant and terminal solderable.

THERMAL RESISTANCE: 1.5°C/W (Typical) junction to base.

POLARITY: Standard Polarity units are connected anode to case. Reverse polarity (cathode to case is indicated by a red dot on the base plate. (Suffix R)

WEIGHT: 15 grams.

MOUNTING HARDWARE: See page 2-9.

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